



March 1996

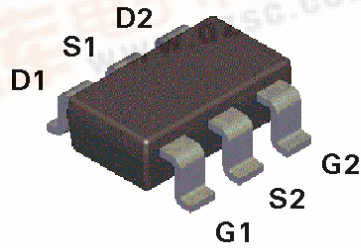
NDC7002N Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

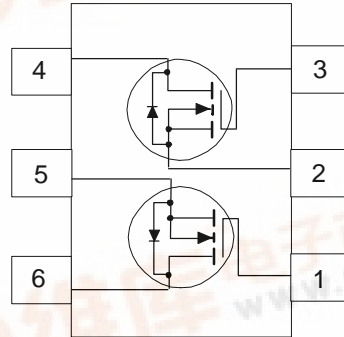
These dual N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been designed to minimize on-state resistance, provide rugged and reliable performance and fast switching. These devices is particularly suited for low voltage applications requiring a low current high side switch.

Features

- 0.51A, 50V, $R_{DS(ON)} = 2\Omega @ V_{GS}=10V$
- High density cell design for low $R_{DS(ON)}$.
- Proprietary SuperSOT™-6 package design using copper lead frame for superior thermal and electrical capabilities.
- High saturation current.



SOT-6 (SuperSOT™-6)

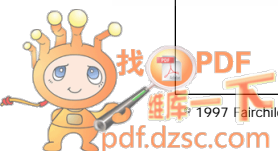


Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	NDC7002N	Units	
V_{DSS}	Drain-Source Voltage	50	V	
V_{GSS}	Gate-Source Voltage - Continuous	20	V	
I_D	Drain Current - Continuous (Note 1a)	0.51	A	
	- Pulsed	1.5		
P_D	Maximum Power Dissipation (Note 1a)	0.96	W	
		(Note 1b)		0.9
		(Note 1c)		0.7
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$	

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	130	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	60	$^\circ\text{C}/\text{W}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
OFF CHARACTERISTICS							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	50			V	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$			1	μA	
			$T_J = 125^\circ\text{C}$		500		
I_{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA	
I_{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA	
ON CHARACTERISTICS (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	1.9	2.5	V	
			$T_J = 125^\circ\text{C}$	0.8	1.5	2.2	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.51\text{ A}$		1	2	Ω	
			$T_J = 125^\circ\text{C}$		1.7	3.5	
			$V_{GS} = 4.5\text{ V}, I_D = 0.35\text{ A}$		1.6	4	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}$	1.5			A	
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 0.51\text{ A}$		400		mS	
DYNAMIC CHARACTERISTICS							
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		20		pF	
C_{oss}	Output Capacitance			13		pF	
C_{rss}	Reverse Transfer Capacitance			5		pF	
SWITCHING CHARACTERISTICS (Note 2)							
$t_{D(on)}$	Turn - On Delay Time	$V_{DD} = 25\text{ V}, I_D = 0.25\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 25\ \Omega$		6	20	nS	
t_r	Turn - On Rise Time			6	20		
$t_{D(off)}$	Turn - Off Delay Time			11	20		
t_f	Turn - Off Fall Time			5	20		
Q_g	Total Gate Charge	$V_{DS} = 25\text{ V},$ $I_D = 0.51\text{ A}, V_{GS} = 10\text{ V}$		1		nC	
Q_{gs}	Gate-Source Charge			0.19		nC	
Q_{gd}	Gate-Drain Charge			0.33		nC	

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
DRAIN-SOURCE DIODE CHARACTERISTICS						
I_S	Maximum Continuous Source Current				0.51	A
I_{SM}	Maximum Pulse Source Current (Note 2)				1.5	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 0.51\text{ A}$ (Note 2)		0.8	1.2	V

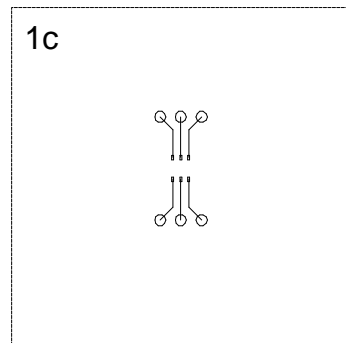
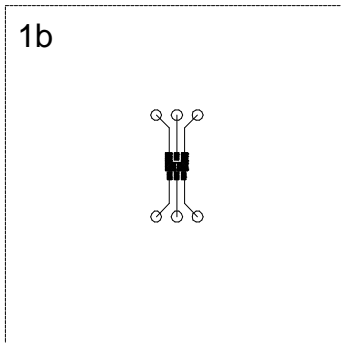
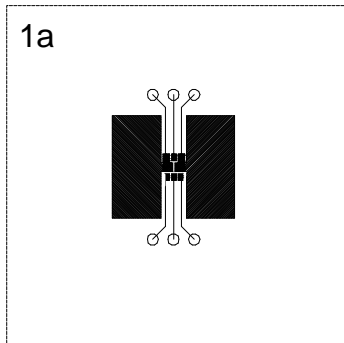
Notes:

- $R_{\theta_{JA}}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta_{JC}}$ is guaranteed by design while $R_{\theta_{CA}}$ is determined by the user's board design.

$$P_D(t) = \frac{T_J - T_A}{R_{\theta_{JA}}} = \frac{T_J - T_A}{R_{\theta_{JC}} + R_{\theta_{CA}}} = I_D^2(t) \times R_{DS(on)} \theta_{TJ}$$

Typical $R_{\theta_{JA}}$ for single device operation using the board layouts shown below on 4.5"x5" FR-4 PCB in a still air environment:

- 130°C/W when mounted on a 0.125 in² pad of 2oz copper.
- 140°C/W when mounted on a 0.005 in² pad of 2oz copper.
- 180°C/W when mounted on a 0.0015 in² pad of 2oz copper.



Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Typical Electrical Characteristics

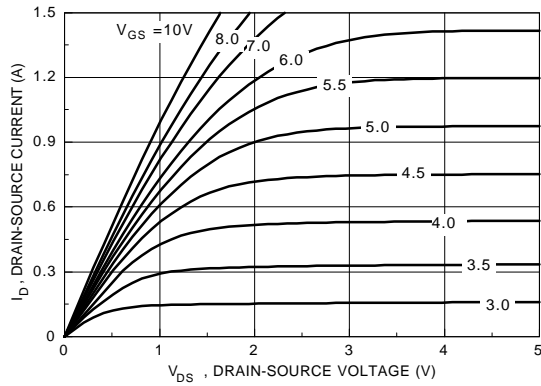


Figure 1. On-Region Characteristics.

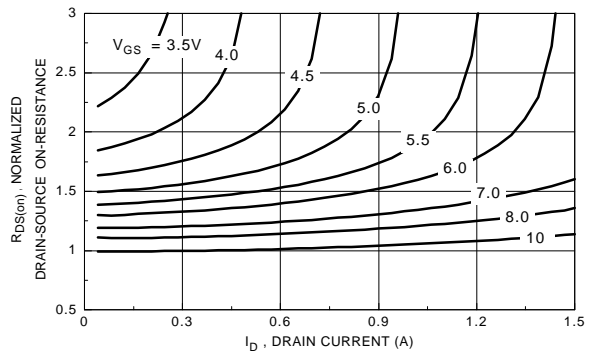


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

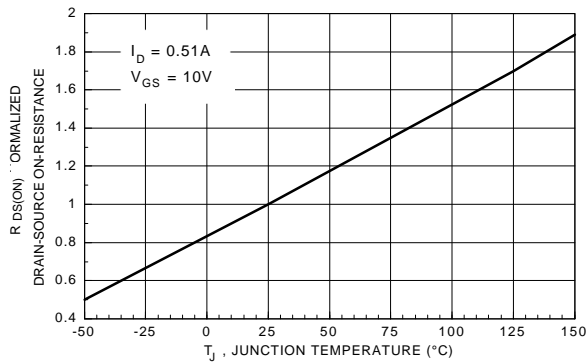


Figure 3. On-Resistance Variation with Temperature.

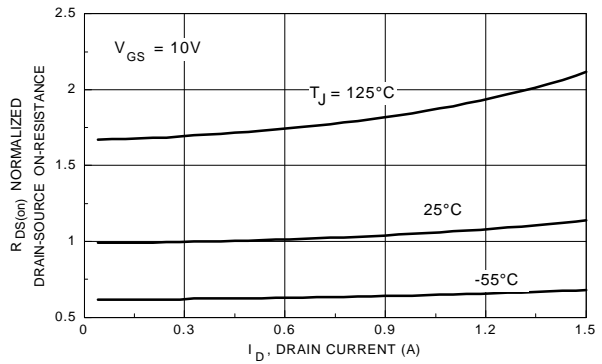


Figure 4. On-Resistance Variation with Drain Current and Temperature.

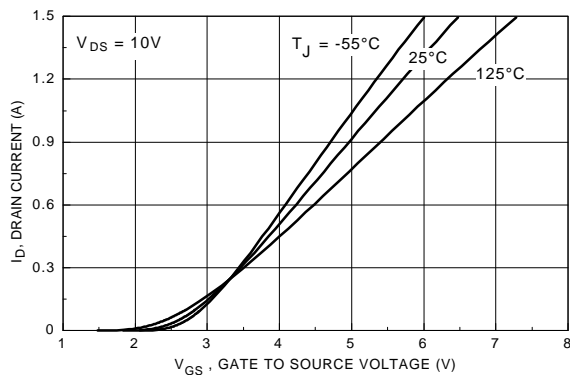


Figure 5. Transfer Characteristics.

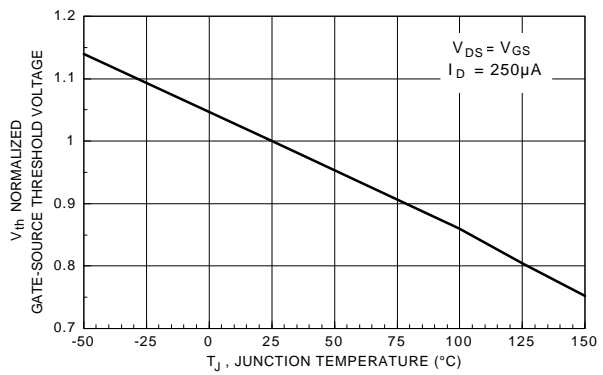


Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics (continued)

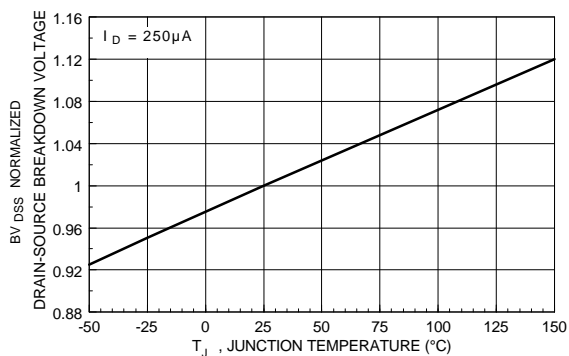


Figure 7. Breakdown Voltage Variation with Temperature.

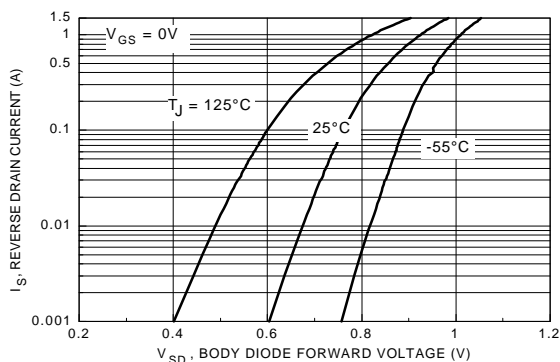


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

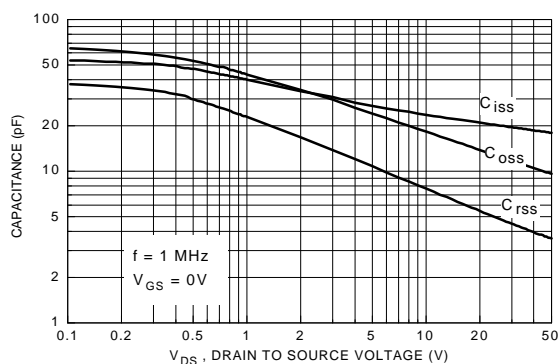


Figure 9. Capacitance Characteristics.

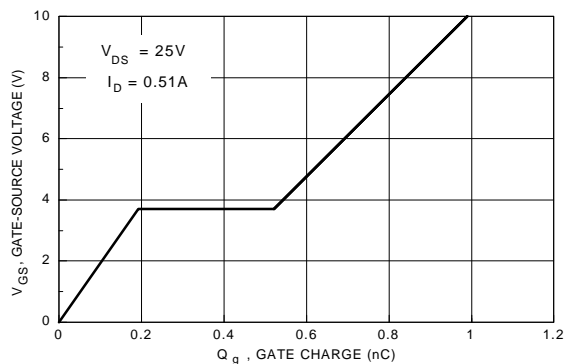


Figure 10. Gate Charge Characteristics.

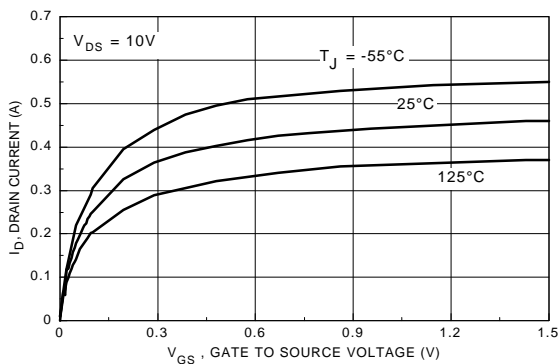


Figure 11. Transconductance Variation with Drain Current and Temperature.

Typical Thermal Characteristics

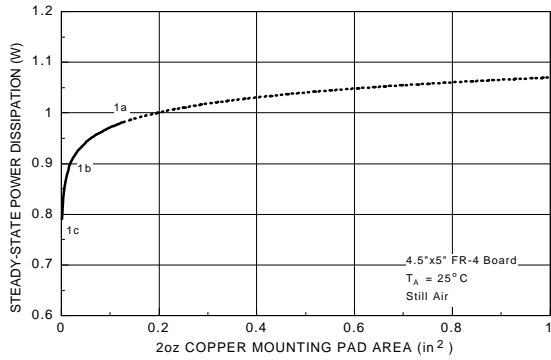


Figure 12. SOT-6 Dual Package Maximum Steady-State Power Dissipation versus Copper Mounting Pad Area.

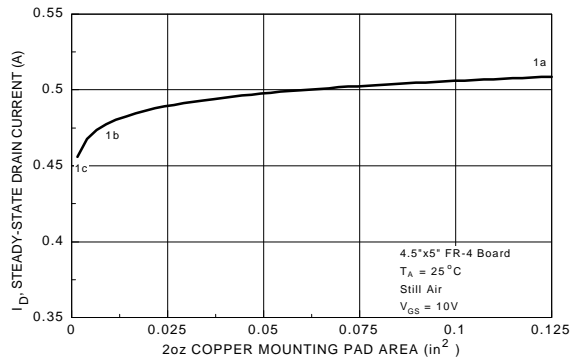


Figure 13. Maximum Steady-State Drain Current versus Copper Mounting Pad Area.

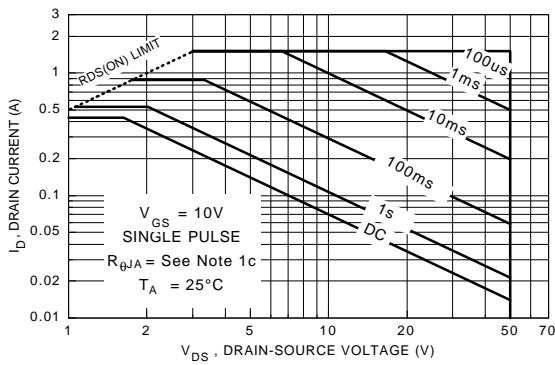


Figure 14. Maximum Safe Operating Area.

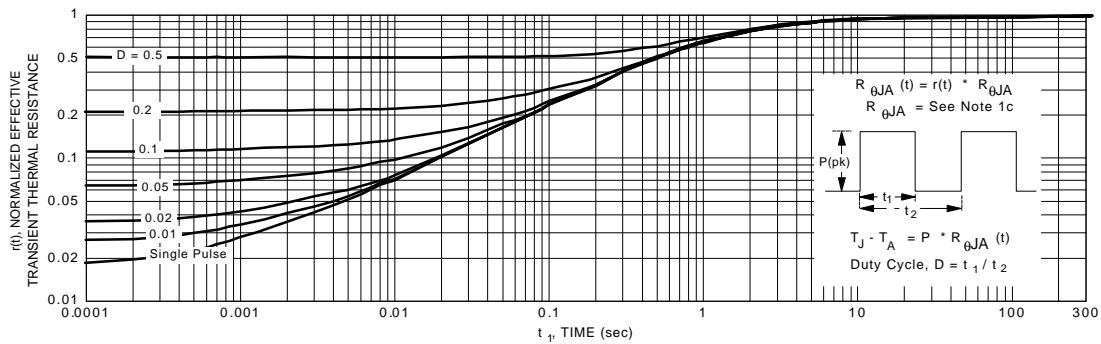


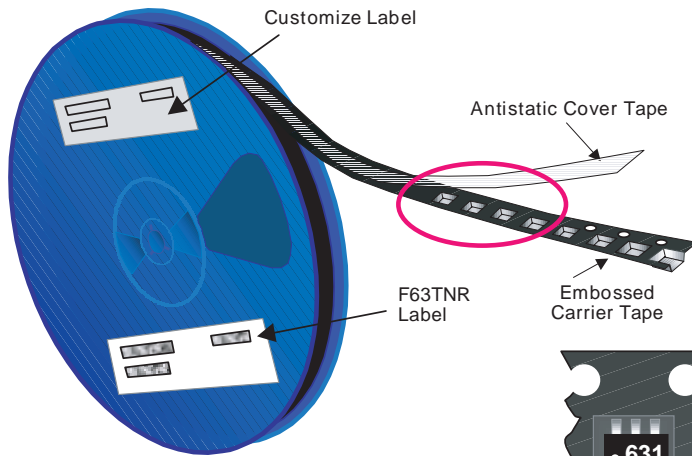
Figure 15. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c. Transient thermal response will change depending on the circuit board design.

SuperSOT™-6 Tape and Reel Data and Package Dimensions



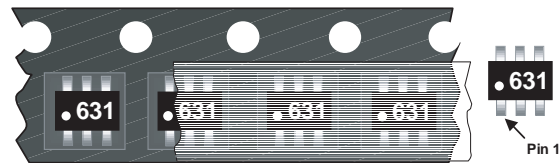
SSOT-6 Packaging Configuration: Figure 1.0



Packaging Description:

SSOT-6 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 177cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 10,000 units per 13" or 330cm diameter reel. This and some other options are described in the Packaging Information table.

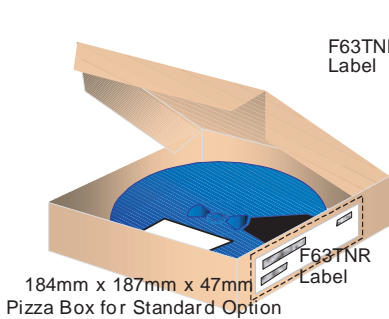
These full reels are individually barcode labeled and placed inside a pizza box (illustrated in figure 1.0) made of recyclable corrugated brown paper with a Fairchild logo printing. One pizza box contains three reels maximum. And these pizza boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.



SSOT-6 Unit Orientation

SSOT-6 Packaging Information		
Packaging Option	Standard (no flow code)	D87Z
Packaging type	TNR	TNR
Qty per Reel/Tube/Bag	3,000	10,000
Reel Size	7" Dia	13"
Box Dimension (mm)	184x187x47	343x343x64
Max qty per Box	9,000	30,000
Weight per unit (gm)	0.0158	0.0158
Weight per Reel (kg)	0.1440	0.4700
Note/Comments		

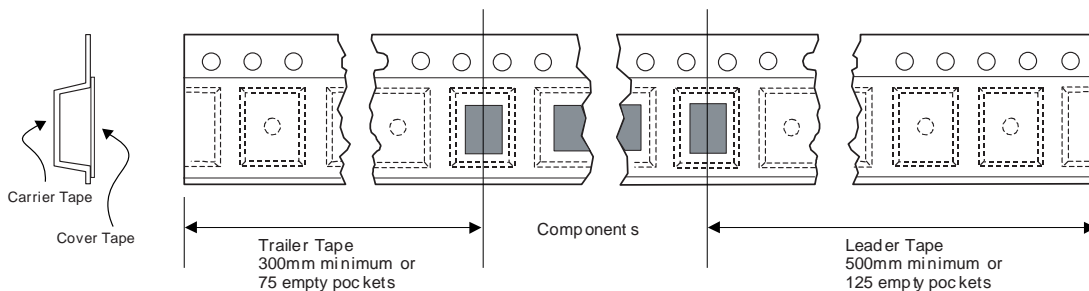
343mm x 342mm x 64mm Intermediate box for D87Z Option



F63TNR Label sample

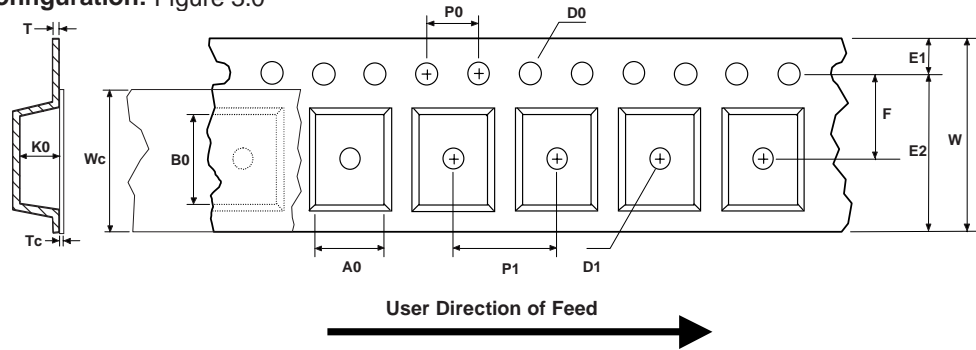


SSOT-6 Tape Leader and Trailer Configuration: Figure 2.0



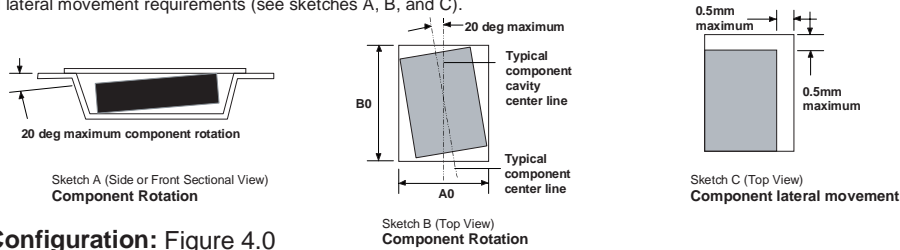
SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

SSOT-6 Embossed Carrier Tape Configuration: Figure 3.0

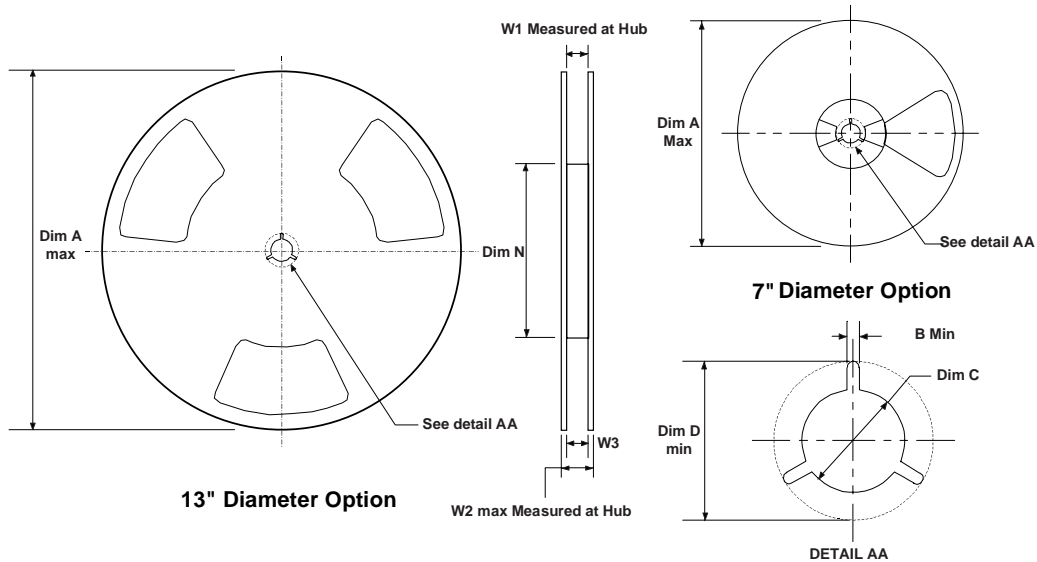


Dimensions are in millimeter														
Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
SSOT-6 (8mm)	3.23 ±0.10	3.18 ±0.10	8.0 ±0.3	1.55 ±0.05	1.125 ±0.125	1.75 ±0.10	6.25 min	3.50 ±0.05	4.0 ±0.1	4.0 ±0.1	1.37 ±0.10	0.255 ±0.150	5.2 ±0.3	0.06 ±0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



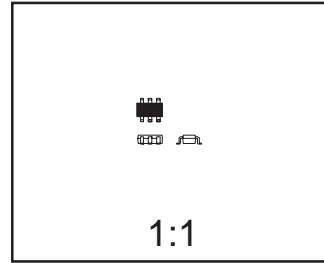
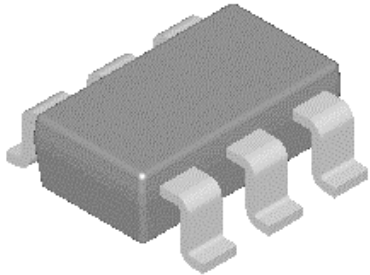
SSOT-6 Reel Configuration: Figure 4.0



Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

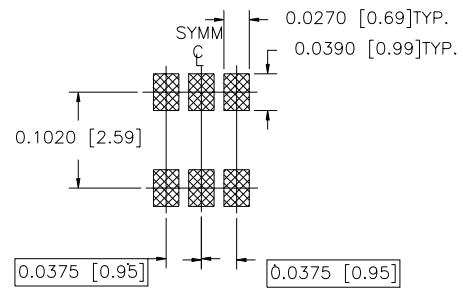
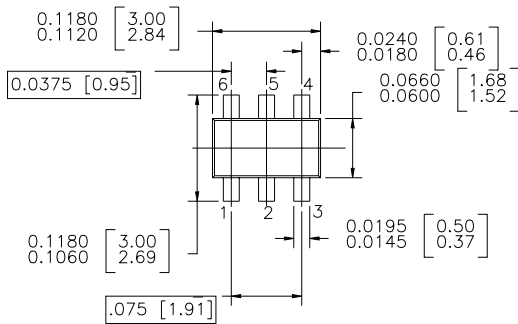
SuperSOT -6 (FS PKG Code 31, 33)



Scale 1:1 on letter size paper

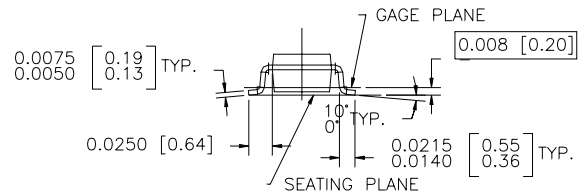
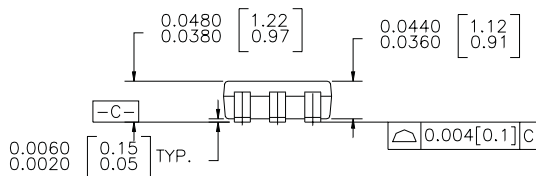
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0158



LAND PATTERN RECOMMENDATION

CONTROLLING DIMENSION IS INCH
VALUES IN [] ARE MILLIMETERS



SUPER SOT 6 LEADS

NOTES : UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH : 150 MICROINCHES 93.81 MICROMETERS)
MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

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FACT Quiet Series™	QS™	
FAST®	Quiet Series™	
FASTr™	SuperSOT™-3	
GTO™	SuperSOT™-6	
HiSeC™	SuperSOT™-8	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.